

	1. contact adj drain and source to nearil semi-insulating adj layer	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
	2. semiconductor adj layer nearil gate and insulating nearil above nearil gate and electrode and source and drain and electrode nearil semi-insulating adj layer	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
	3. drain adj electrode nearil reducing nearil size or area	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
	4. contact adj hole nearil edge or side nearil drain adj electrode and drain adj electrode nearil reducing nearil size or area	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
	5. contact adj hole nearil drain adj electrode nearil pixel adj region	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
	6. contact adj hole nearil over nearil (drain adj electrode) nearil over nearil pixel adj region	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:50
3'6"	7. contact adj hole nearil 'passivation' nearil exposed (drain adj electrode) nearil insulating	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:44
	20. contact adj hole nearil 'passivation' nearil exposed nearil (drain adj electrode) nearil (insulating)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/14 17:44
	8. (contact adj hole nearil formed nearil over nearil 'drain and pixel'	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/03/15 08:53
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